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semiconductor and (trench same oxide same fluorine)	205

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IBM Technical Disclosure Bulletins	▼

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DB=USPT; PLUR=YES; OP=ADJ

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DB=DWPI; PLUR=YES; OP=ADJ

<u>L1</u>	semiconductor and trench and (((HDP or (high adj density adj plasma)) adj oxide) same fluorine)	0	<u>L1</u>
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Search Results - Record(s) 1 through 9 of 9 returned.

☐ 1. Document ID: US 6541349 B2

L2: Entry 1 of 9

File: USPT

Apr 1, 2003

US-PAT-NO: 6541349

DOCUMENT-IDENTIFIER: US 6541349 B2

TITLE: Shallow trench isolation using non-conformal dielectric and planarization

DATE-ISSUED: April 1, 2003

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Arthanari; Senthilkumar	San Jose	CA		
Mei; Shaw-Ning	Poughkeepsie	NY		
Vishnesky; Edward J.	Poughkeepsie	NY		

US-CL-CURRENT: 438/424; 257/E21.548, 438/427

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KAMC	Draw Desc	Image
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☐ 2. Document ID: US 6452224 B1

L2: Entry 2 of 9

File: USPT

Sep 17, 2002

US-PAT-NO: 6452224

DOCUMENT-IDENTIFIER: US 6452224 B1

TITLE: Method for manufacture of improved deep trench eDRAM capacitor and structure produced thereby

DATE-ISSUED: September 17, 2002

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Mandelman; Jack A.	Stormville	NY		
Radens; Carl J.	LaGrangeville	NY		

US-CL-CURRENT: 257/296; 257/301, 257/303, 257/306, 257/E21.652, 257/E27.096, 257/E29.346

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KAMC	Draw Desc	Image
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☐ 3. Document ID: US 6396113 B1

L2: Entry 3 of 9

File: USPT

May 28, 2002

US-PAT-NO: 6396113
DOCUMENT-IDENTIFIER: US 6396113 B1

TITLE: Active trench isolation structure to prevent punch-through and junction leakage

DATE-ISSUED: May 28, 2002

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Fujinaga; Masato	Tokyo			JP
Kunikiyo; Tatsuya	Tokyo			JP

US-CL-CURRENT: 257/397; 257/E21.546, 257/E21.572, 257/E21.628, 257/E29.009, 438/297,
438/439

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC	Draw Desc	Image
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☐ 4. Document ID: US 6361705 B1

L2: Entry 4 of 9

File: USPT

Mar 26, 2002

US-PAT-NO: 6361705
DOCUMENT-IDENTIFIER: US 6361705 B1

TITLE: Plasma process for selectively etching oxide using fluoropropane or fluoropropylene

DATE-ISSUED: March 26, 2002

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Wang; Ruiping	Fremont	CA		
Yin; Gerald Z.	Cupertino	CA		
Lu; Hao A.	San Mateo	CA		
Wu; Robert W.	Pleasanton	CA		
Ding; Jian	San Jose	CA		

US-CL-CURRENT: 216/39; 216/67, 216/72, 216/79, 216/80, 257/E21.252, 438/719, 438/723,
438/738, 438/743, 438/744

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC	Draw Desc	Image
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☐ 5. Document ID: US 6352917 B1

L2: Entry 5 of 9

File: USPT

Mar 5, 2002

US-PAT-NO: 6352917
DOCUMENT-IDENTIFIER: US 6352917 B1

TITLE: Reversed damascene process for multiple level metal interconnects

DATE-ISSUED: March 5, 2002

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Gupta; Subhash	Singapore			SG
Zhou; Mei-Sheng	Singapore			SG
Chooi; Simon	Singapore			SG
Hong; Sangki	Singapore			SG

US-CL-CURRENT: 438/622; 438/633, 438/638, 438/639

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KWIC	Draw Desc	Image
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☐ 6. Document ID: US 6270353 B1

L2: Entry 6 of 9

File: USPT

Aug 7, 2001

US-PAT-NO: 6270353

DOCUMENT-IDENTIFIER: US 6270353 B1

TITLE: Low cost shallow trench isolation using non-conformal dielectric material

DATE-ISSUED: August 7, 2001

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Andrews; John W.	Wappinger Falls	NY		
Hwang; Bao T.	Poughkeepsie	NY		
Landis; Howard S.	Underhill	VT		
Mei; Shaw-Ning	Poughkeepsie	NY		
Tyler; James M.	Lagrangeville	NY		
Vishnesky; Edward J.	Poughkeepsie	NY		

US-CL-CURRENT: 434/424; 257/E21.548, 438/427

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KWIC	Draw Desc	Image
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☐ 7. Document ID: US 6183655 B1

L2: Entry 7 of 9

File: USPT

Feb 6, 2001

US-PAT-NO: 6183655

DOCUMENT-IDENTIFIER: US 6183655 B1

TITLE: Tunable process for selectively etching oxide using fluoropropylene and a hydrofluorocarbon

DATE-ISSUED: February 6, 2001

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Wang; Ruiping	Fremont	CA		
Yin; Gerald Z.	Cupertino	CA		
Wu; Robert W.	Pleasanton	CA		
Ding; Jian	San Jose	CA		

US-CL-CURRENT: 216/68; 216/72, 216/80, 257/E21.252, 438/723, 438/738, 438/743

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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☐ 8. Document ID: US 6074959 A

L2: Entry 8 of 9

File: USPT

Jun 13, 2000

US-PAT-NO: 6074959

DOCUMENT-IDENTIFIER: US 6074959 A

TITLE: Method manifesting a wide process window and using hexafluoropropane or other hydrofluoropropanes to selectively etch oxide

DATE-ISSUED: June 13, 2000

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Wang; Ruiping	Fremont	CA		
Yin; Gerald Z.	Cupertino	CA		
Wu; Robert W.	Pleasanton	CA		
Ding; Jian	San Jose	CA		

US-CL-CURRENT: 438/738; 216/68, 216/72, 216/79, 257/E21.252, 438/723

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KAMC	Draw Desc	Image
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☐ 9. Document ID: US 5955380 A

L2: Entry 9 of 9

File: USPT

Sep 21, 1999

US-PAT-NO: 5955380

DOCUMENT-IDENTIFIER: US 5955380 A

TITLE: Endpoint detection method and apparatus

DATE-ISSUED: September 21, 1999

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Lee; Gill Yong	Fishkill	NY		

US-CL-CURRENT: 438/706; 257/E21.582, 438/735, 438/737, 438/738, 438/740

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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